



迈拓电子
MAITUO ELECTRONIC

MT2302 Plastic-Encapsulate MOSFETS

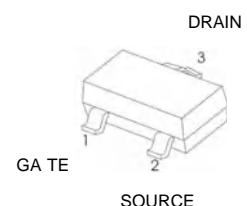
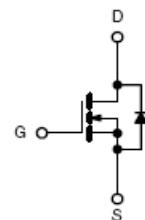
FEATURE

TrenchFET Power MOSFET

APPLICATIONS

Load Switch for Portable Devices

DC/DC Converter



MARKING: 2302

SOT-23

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	2.3	A
Continuous Source-Drain Current(Diode Conduction)	I_S	0.6	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	357	°C/W
Operating Junction	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~+150	



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Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 10\mu\text{A}$	20			V
Gate-threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.5	0.65	1.0	
Gate-body leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 8\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Drain-source on-resistance ^a	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 2.5\text{A}$		0.055	0.085	Ω
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 2.1\text{A}$		0.070	0.125	
Forward transconductance ^a	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_{\text{D}} = 2.5\text{A}$		8		S
Diode forward voltage	V_{SD}	$I_{\text{S}} = 0.94\text{A}, V_{\text{GS}} = 0\text{V}$		0.76	1.2	V
Dynamic						
Total gate charge	Q_g	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 2.5\text{A}$		4.0	10	nC
Gate-source charge	Q_{gs}			0.65		
Gate-drain charge	Q_{gd}			1.5		
Input capacitance ^b	C_{iss}	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		300		pF
Output capacitance ^b	C_{oss}			120		
Reverse transfer capacitance ^b	C_{rss}			80		
Switching^b						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, R_L = 5.5\Omega, I_{\text{D}} \approx 2.5\text{A}, V_{\text{GEN}} = 4.5\text{V}, R_{\text{g}} = 6\Omega$		7	15	ns
Rise time	t_r			55	80	
Turn-off delay time	$t_{\text{d}(\text{off})}$			16	60	
Fall time	t_f			10	25	

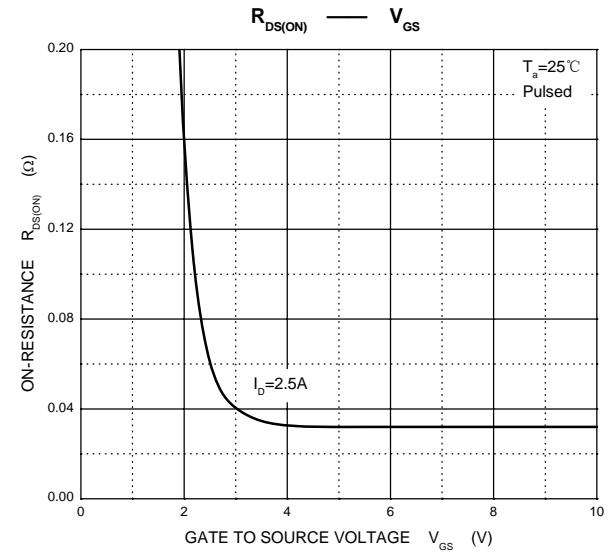
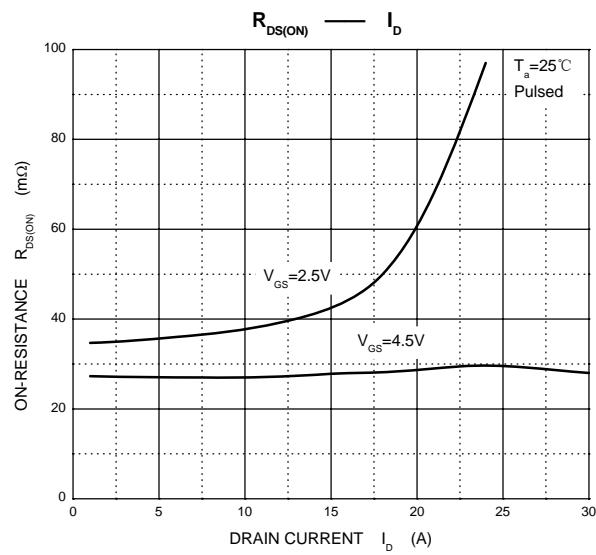
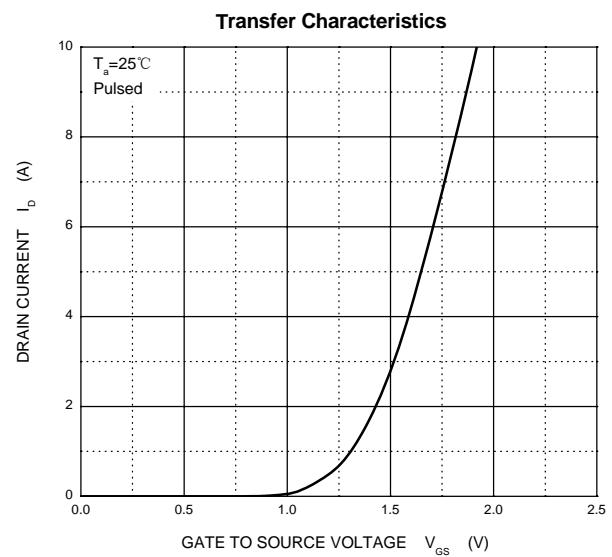
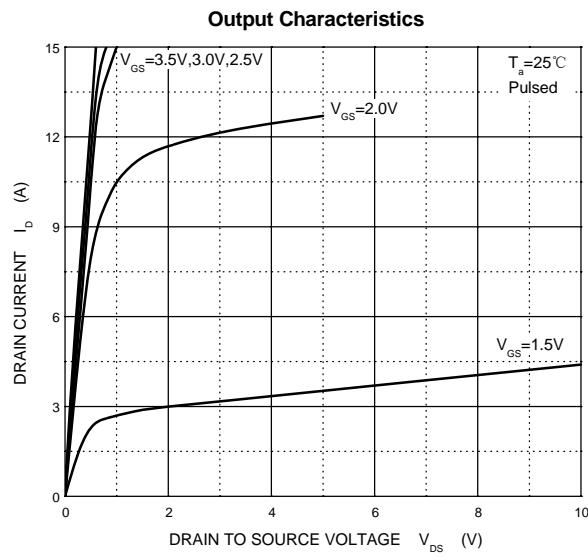
Notes :

- Pulse Test : Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- These parameters have no way to verify.



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Typical Characteristics



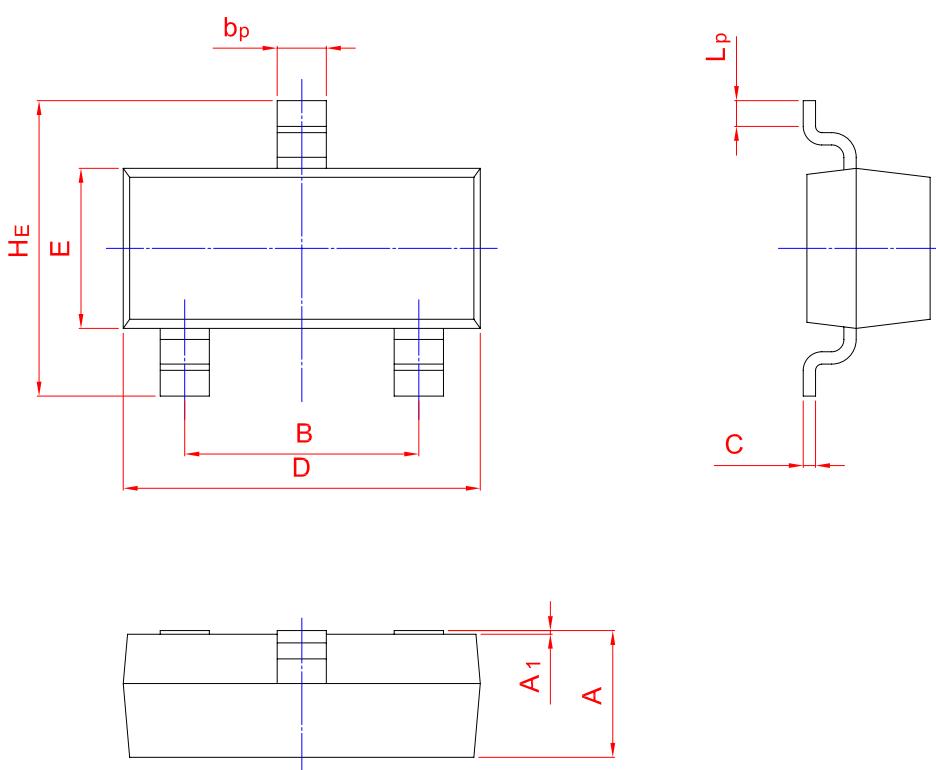


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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20